TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

T C 7 M H 2 5 7 F K

Quad 2-Channel Multiplexer (3-State)

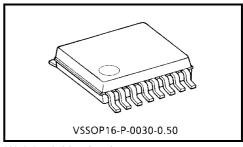
The TC7MH257FK is an advanced high speed CMOS multiplexer fabricated with silicon gate C^2 MOS technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

It is composed of four independent 2-channel multiplexers with common SELECT and $\overline{OUTPUTENABLE}$ (\overline{OE}).

If \overline{OE} is set low, the outputs are held in a high-impedance state. When SELECT is set low, "A" data inputs are enabled.

Conversely, when SELECT is high, "B" data inputs are enabled.



Weight: 0.02 g (typ.)

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

- High speed: $t_{pd} = 3.6 \text{ ns (typ.)} (V_{CC} = 5 \text{ V})$
- Low power dissipation: $ICC = 4 \mu A \text{ (max) (Ta} = 25^{\circ}C)$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: $t_pLH \approx t_pHL$
- Wide operating voltage range: V_{CC} (opr) = $2 \sim 5.5 \text{ V}$
- Low noise: VOLP = 0.8 V (max)
- Pin and function compatible with 74ALS257

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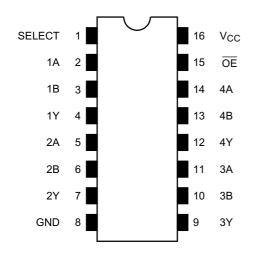
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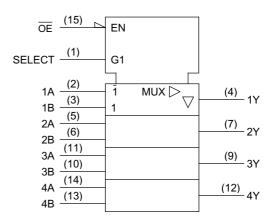
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Pin Assignment (top view)



IEC Logic Symbol



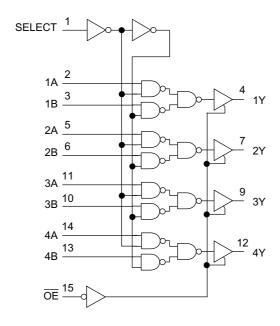
Truth Table

	Outpute			
ŌĒ	Select	Α	Outputs	
Н	Х	Х	Х	Z
L	L	L	Х	L
L	L	Н	Х	Н
L	Н	Х	L	L
L	Н	Х	Н	Н

X: Don't care

Z: High impedance

System Diagram





Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	lok	±20	mA
DC output current	I _{OUT}	±25	mA
DC V _{CC} /ground current	Icc	±50	mA
Power dissipation	PD	180	mW
Storage temperature	T _{stg}	-65~150	°C

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0~5.5	V
Input voltage	V _{IN}	0~5.5	V
Output voltage	Vout 0~Vcc		٧
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	$0\sim100 \ (V_{CC}=3.3\pm0.3 \ V)$	ns/V
input rise and rail diffe	ui/uv	$0\sim20 \ (V_{CC}=5\pm0.5 \ V)$	115/V



Electrical Characteristics

DC Characteristics

Characteristics		Symbol Test Condition		Candition		Ta = 25°C			Ta = -40~85°C		Unit
		Symbol	rest Condition		V _{CC} (V)	Min	Тур.	Max	Min	Max	Offic
			_		2.0	1.50	_	_	1.50	_	
	High level	V_{IH}			3.0~5.5	V _{CC} × 0.7	_	_	V _{CC} × 0.7	_	V
Input voltage						_	_	0.50	_	0.50	V
	Low level	V _{IL}	_		3.0~5.5		_	V _{CC} × 0.3	_	V _{CC} ×0.3	
	High level	Vон		$I_{OH} = -50 \mu A$	2.0	1.9	2.0	_	1.9	_	
			V _{IN} = V _{IH} or V _{IL}		3.0	2.9	3.0	_	2.9	_	٧
Output voltage					4.5	4.4	4.5		4.4	_	
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48		
				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_		3.80	_	
Output Voltage	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}		2.0	_	0	0.1		0.1	V
				$I_{OL} = 50 \mu A$	3.0	_	0	0.1	_	0.1	
					4.5	_	0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0	_	_	0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$	4.5	_	_	0.36	_	0.44	
3-state output off-state current		l _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		5.5	_		±0.25	_	±2.50	μА
Input leakage cu	rrent	I _{IN}	V _{IN} = 5.5 V or GND		0~5.5		_	±0.1	_	±1.0	μΑ
Quiescent supply current		Icc	V _{IN} = V _{CC} or GND		5.5	_	_	4.0	_	40.0	μΑ



AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -40~85°C		- Unit
Characteristics	Symbol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Onit
Propagation delay time	t _{pLH}		3.3 ± 0.3	15	_	5.8	9.3	1.0	11.0	ns
				50	_	8.3	12.8	1.0	14.5	
(A, B-Y)	t _{pHL}	_	5.0 ± 0.5	15		3.6	5.9	1.0	7.0	113
			3.0 ± 0.5	50		5.1	7.9	1.0	9.0	
			3.3 ± 0.3	15		7.0	11.0	1.0	13.0	
Propagation delay time	t _{pLH}	_		50		9.5	14.5	1.0	16.5	ns
(SELECT-Y)	tpHL		5.0 ± 0.5	15		4.0	6.8	1.0	8.0	
				50	_	5.5	8.8	1.0	10.0	
	t _{pZL} t _{pZH}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	15	_	6.7	10.5	1.0	12.5	- ns
3-state output enable time				50		9.2	14.0	1.0	16.0	
3-State output enable time			5.0 ± 0.5	15	_	3.6	6.8	1.0	8.0	
			3.0 ± 0.5	50	_	5.1	8.8	1.0	10.0	
3-state output disable time	t _{pLZ} t _{pHZ}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	50	_	8.6	12.0	1.0	13.5	ns
3-state output disable time			5.0 ± 0.5	50	_	5.7	7.9	1.0	9.0	115
Input capacitance	C _{IN}	-	_		_	4	10	_	10	pF
Output capacitance	C _{OUT}	-	_		_	6	_		_	pF
Power dissipation capacitance	C _{PD}			(Note)	_	23	_	_	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

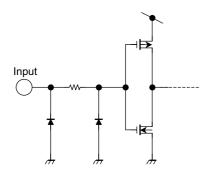
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{ (per bit)}$

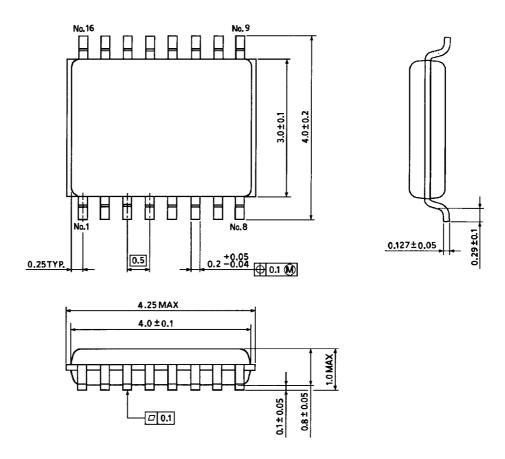
Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition		Ta = 25°C		Unit
Gilaracteristics	Syllibol	rest Condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	0.3	0.8	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-0.3	-0.8	V
Minimum high level dynamic input voltage $V_{\mbox{\scriptsize IH}}$	V _{IHD}	C _L = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage V_{IL}	V _{ILD}	C _L = 50 pF	5.0	_	1.5	V

Input Equivalent Circuit



Package Dimensions



Weight: 0.02 g (typ.)